Product data sheet

1. Product profile

1.1 General description

Planar PIN diode in a SOD882T leadless ultra small plastic SMD package.

1.2 Features

- High voltage, current controlled
- Low diode capacitance
- Low diode forward resistance (low loss)
- Very low series inductance
- RF resistor for RF switches

1.3 Applications

- RF attenuators and switches
- Band switch for TV tuners
- Series diode for mobile communication transmit-receive switch

2. Pinning information

Table 1. Discrete pinning

	3	
Pin	Description	Simplified outline Symbol
1	cathode	<u>U</u>
2	anode	1 2
		Transparent sym006 top view

^[1] The marking bar indicates the cathode.

3. Ordering information

Table 2. Ordering information

Type number	Package	ackage				
	Name	Description	Version			
BAP65LX	-	leadless ultra small plastic package; 2 terminals; body 1 \times 0.6 \times 0.4 mm	SOD882T			



4. Marking

Table 3. Marking

Type number	Marking code
BAP65LX	LF

5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{R}	reverse voltage		-	30	V
I _F	forward current		-	100	mA
P _{tot}	total power dissipation	$T_{sp} = 90 ^{\circ}C$	-	135	mW
T_{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-65	+150	°C

6. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point		78	K/W

7. Characteristics

Table 6. Characteristics

 T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{F}	forward voltage	$I_F = 50 \text{ mA}$	-	0.9	1.1	V
I _R	reverse current	V _R = 20 V	-	-	20	nA
C _d	diode capacitance	see Figure 1; f = 1 MHz;				
		$V_R = 0 V$	-	0.61	-	pF
		$V_R = 1 V$	-	0.48	0.85	pF
		$V_R = 3 V$	-	0.43	0.7	pF
		V _R = 20 V	-	0.37	-	pF
r _D diode forward resistance		see Figure 2; f = 100 MHz;				
		I _F = 1 mA	-	0.94	-	Ω
		$I_F = 5 \text{ mA}$	-	0.58	0.95	Ω
		$I_F = 10 \text{ mA}$	-	0.49	0.9	Ω
		$I_{F} = 100 \text{ mA}$	-	0.35	-	Ω

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Table 6.
Characteristics ...continued
 T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
ISL	isolation	see Figure 3; V _R = 0 V;				
		f = 900 MHz	-	10	-	dB
		f = 1800 MHz	-	5.5	-	dB
		f = 2450 MHz	-	3.9	-	dB
L _{ins} insertion loss	insertion loss	see Figure 4; I _F = 1 mA;				
		f = 900 MHz	-	0.09	-	dB
		f = 1800 MHz	-	0.09	-	dB
		f = 2450 MHz	-	0.10	-	dB
L _{ins} insertion loss	insertion loss	see Figure 4; I _F = 5 mA;				
		f = 900 MHz	-	0.06	-	dB
	f = 1800 MHz	-	0.07	-	dB	
	f = 2450 MHz	-	0.08	-	dB	
L _{ins}	insertion loss	see Figure 4; I _F = 10 mA;				
		f = 900 MHz	-	0.06	-	dB
		f = 1800 MHz	-	0.07	-	dB
		f = 2450 MHz	-	0.08	-	dB
L _{ins}	insertion loss	see Figure 4; I _F = 100 mA;				
		f = 900 MHz	-	0.05	-	dB
		f = 1800 MHz	-	0.06	-	dB
		f = 2450 MHz	-	0.07	-	dB
τ _L	charge carrier life time	when switched from I $_{F}$ = 10 mA to I $_{R}$ = 6 mA; R $_{L}$ = 100 $\Omega;$ measured at I $_{R}$ = 3 mA	-	0.18	-	μs
-s	series inductance	$I_F = 100 \text{ mA}$; $f = 100 \text{ MHz}$	-	0.4	-	nΗ

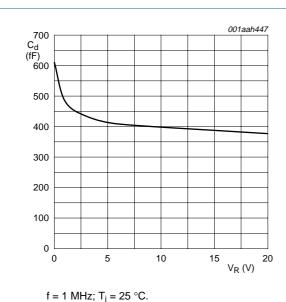
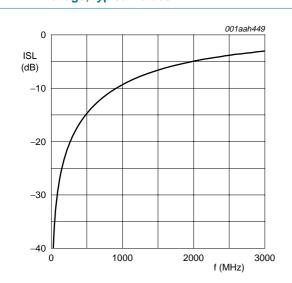


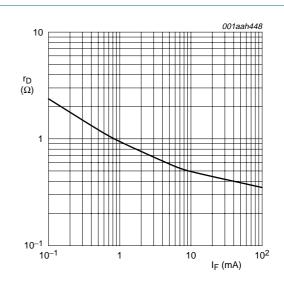
Fig 1. Diode capacitance as a function of reverse voltage; typical values



T_{amb} = 25 °C

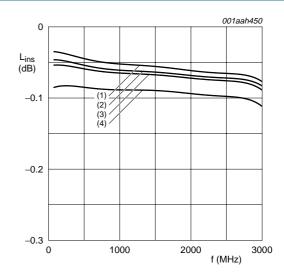
Diode zero biased and inserted in series with a 50 Ω stripline circuit





 $f = 100 \text{ MHz}; T_i = 25 \,^{\circ}\text{C}.$

Fig 2. Forward resistance as a function of forward current; typical values



T_{amb} = 25 °C

- (1) $I_F = 100 \text{ mA}$
- (2) $I_F = 10 \text{ mA}$
- (3) $I_F = 5 \text{ mA}$
- (4) $I_F = 1 \text{ mA}$

Diode inserted in series with a 50 Ω stripline circuit and biased via the analyzer Tee network

Fig 4. Insertion loss of the diode as a function of frequency; typical values

8. Package outline

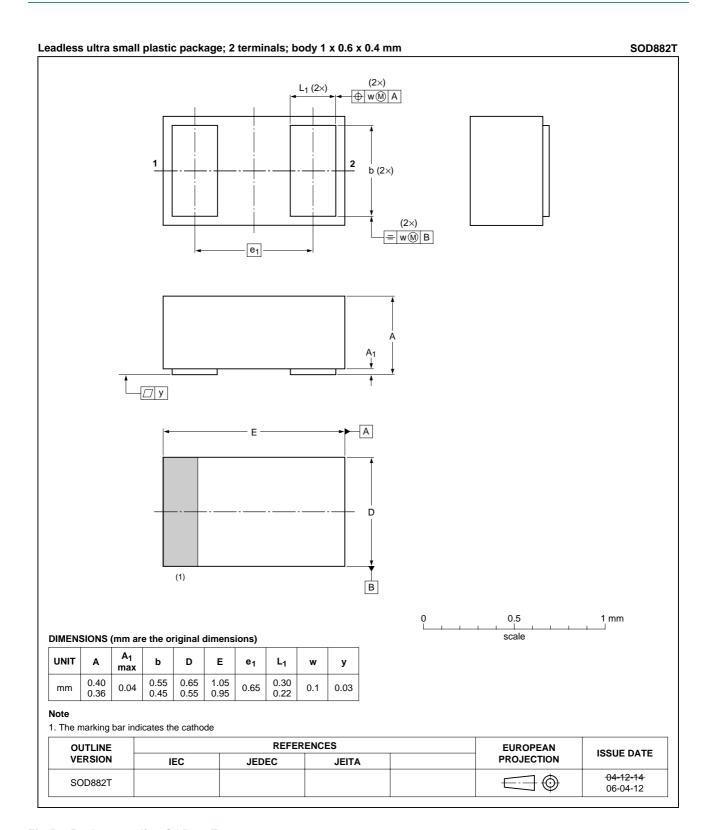


Fig 5. Package outline SOD882T

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Abbreviations

Table 7. **Abbreviations**

Acronym	Description
PIN	P-type, Intrinsic, N-type
SMD	Surface Mounted Device
RF	Radio Frequency

10. Revision history

Table 8. **Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
BAP65LX_1	20071211	Product data sheet	-	-

11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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13. Contents

1	Product profile
1.1	General description
1.2	Features
1.3	Applications
2	Pinning information 1
3	Ordering information 1
4	Marking 2
5	Limiting values
6	Thermal characteristics 2
7	Characteristics
8	Package outline 5
9	Abbreviations 6
10	Revision history 6
11	Legal information 7
11.1	Data sheet status
11.2	Definitions
11.3	Disclaimers
11.4	Trademarks 7
12	Contact information 7
13	Contents

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